UNIT:mm

# ISA1530AC1 ISA1603AM1

OUTLINE DRAWING

FOR LOW FREQUENCY AMPLIFY APPLICATION SILICON PNP EPITAXIAL TYPE



ISA1530AC1 ISA1603AM1 is super mini package resin sealed silicon PNP epitaxial type transistor.

These are designed for low frequency voltage amplify application .

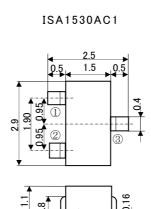
### FEATURE

•Excellent linearity of DC forward current gain.

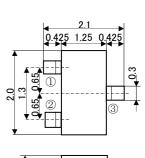
 Small collector to emitter saturation voltage VCE(sat)=-0.3Vmax

#### APPLICATION

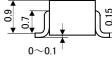
For small type machine low frequency voltage amplify application.



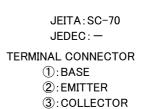
0~0.1



ISA1603AM1

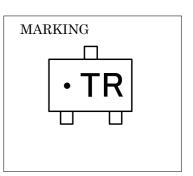


JEITA: SC-59 JEDEC: TO-236 resemblance TERMINAL CONNECTOR ①:BASE ②:EMITTER ③:COLLECTOR



## MAXIMUM RATINGS(Ta=25°C)

Symbol	Parameter	Rat	UNIT
	Farameter	ISA1530AC1	ISA1603AM1
V <sub>CBO</sub>	Collector to Base voltage	I	V
V <sub>EBO</sub>	Collector to Emitter voltage	-	V
V <sub>CEO</sub>	Emitter to Base voltage	-	V
Ι <sub>c</sub>	Collector current	-1	mA
Pc	Collector dissipation	2	mW
Tj	Junction temperature	+1	S
Tstg	Storage temperature	-55~	°C



### ELECTRICAL CHARACTERISTICS (Ta=25°C)

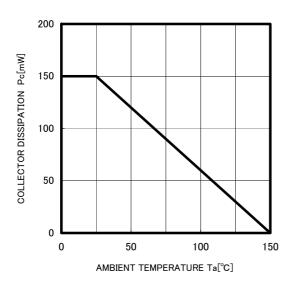
Symbol	Parameter	Test conditions		Limits			UNIT		
					Min	Ave	Max	UNIT	
$V_{(BR)CEO}$	Collector to Emitter Breakdown voltage	$I_{c} = -100 \mu A, R_{BE} = \infty$			-50			V	
I <sub>CBO</sub>	Collector cut off current	$V_{cB} = -60V, I_{E} = 0$					-0.1	μA	
I <sub>EBO</sub>	Emitter cut off current	$V_{EB}$ =-4V, I <sub>c</sub> =0					-0.1	μA	
h <sub>FE</sub> *	DC forward current gain	V <sub>CE</sub> =-6V, I <sub>C</sub> =-1mA			120		560	-	
h <sub>FE</sub>	DC forward current gain	V <sub>ce</sub> =-6V, I <sub>c</sub> =-0.1mA			70			-	
$V_{CE(sat)}$	Collector to Emitter saturation voltage	I <sub>c</sub> =–100mA, I <sub>B</sub> =–10mA					-0.3	V	
f⊤	Gain bandwidth product	V <sub>ce</sub> =-6V, I <sub>e</sub> =10mA				200		MHz	
Cob	Collector output capacitance	$V_{CB}$ =-6V, I <sub>E</sub> =0,f=1MHz				4.0		pF	
NF	Noise figure	V <sub>CE</sub> =-6V, I <sub>E</sub> =0.3mA f=100Hz, RG=10kΩ					20	dB	
*:It shows hFE classification in below table.			hFE		2	R	0 27	S 270~560	
			nrE	120~270		180~390 2		0~360	

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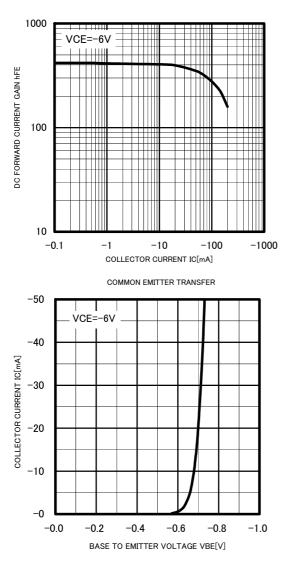
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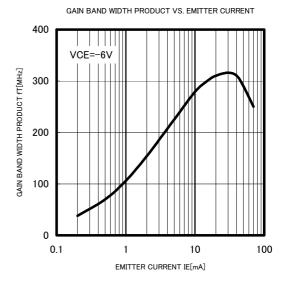
#### TYPICAL CHARACTERISTICS

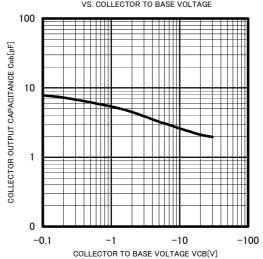
COLLECTOR DISSIPATION VS AMBIENT TEMPERATURE



DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT







COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



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